

Application No.: 09479,483

Docket No.: TKHR4580

CLAIMS AMENDMENTS

Please amend the following claims

D6 1. (currently amended) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

forming a first protective layer on the first device area, wherein the first protective layer prevents the first device area from moisture and scratch;

forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer together formed as first pad spacers;

forming a plurality of oxide material/silicon nitride/oxide material structures on the second device area as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer for at least covering the second device area, wherein a ~~transparency~~ transmittance of the second protective layer is higher than ~~transparency~~ transmittance of the first protective layer.

2. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 1, further including:

forming sequentially a first oxide layer, a silicon nitride layer and a second oxide layer on the substrate;

patterning the second oxide material to form material structures and upper oxide material of the material of the material/silicon nitride/oxide material structures;

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patterning the silicon nitride layer and the first oxide layer to form a silicon nitride/oxide material structure as the first protective layer in the first device area and to form a bottom oxide material and a silicon nitride of the material/silicon nitride/oxide material structures; and

forming a third oxide layer on the substrate as a second protective layer.

3. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the ~~transparency~~ transmittance of the second protective layer is approximately 85%.

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const.
4. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the third oxide layer is approximately 500Å thick.

5. (previously amended) The fabrication method for a multi-layered thin film protective layer according to claim 2, wherein the third oxide layer includes tetra-ethyl-ortho-silicate.

618. (currently amended) A fabrication method for a multi-layered thin film protective layer, which is applicable to a substrate comprising a first device area and a second device area, the method comprising the steps of:

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forming a first protective layer on the first device area, wherein the first protective layer prevents the first device area from moisture and scratch;

forming a plurality of material structures on the first protective layer, the material structures and the underlying first protective layer together formed as first pad spacers;

forming a plurality of multi-layered material structures on the second device area as second pad spacers in the second device area, wherein the second pad spacers are higher than the first protective layer; and

forming a second protective layer at least covering the second device area, wherein a ~~transparency~~ transmittance of the second protective layer is higher than a ~~transparency~~ transmittance of the first protective layer.

719. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim-618, further including:

forming sequentially a first layer, a second layer and a third layer on the substrate;

patterning the third layer to form the material structures and a upper layer of the multi-layered material structures;

patterning the second layer and the first layer to form the first protective layer in the first device area and to form the bottom layers of the material/silicon nitride/oxide material structures; and

forming a second protective layer covering the first device area and the second device area, wherein the second protective layer second protective layer.

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820. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim-618, wherein the second protective layer is thinner than any layers of the multi-layered material structures.

Do 921. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim-618, wherein the first protective layer at least comprises an oxide layer and a silicon oxide layer on the oxide layer.

1022. (currently amended) The fabrication method for a multi-layered thin film protective layer according to claim-618, wherein the second protective layer comprises an oxide layer.
